

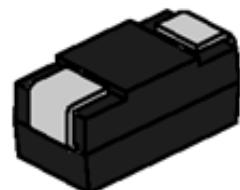


CP4200Sx Series TSS

Rev.4.2

DESCRIPTION:

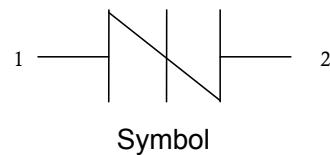
CP4200Sx series are a type of semiconductor component. They are designed to protect baseband equipment from damaging overvoltage transients.



SMB

FEATURES:

- Low profile package.
- Low on-state voltage.
- Excellent capability of absorbing transient surge.
- Quick response to surge voltage (ns Level).
- Eliminates overvoltage caused by fast rising transients.
- Moisture sensitivity level: Level 1.
- Non degenerative.



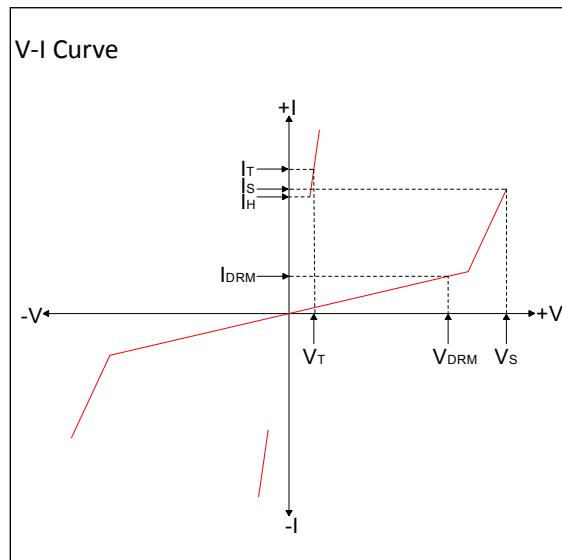
Symbol

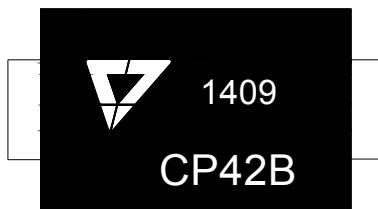
ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, $\text{RH}=45\%-75\%$, unless otherwise noted)

Parameter	Symbol	Value	Unit
Storage temperature range	T_{STG}	-60 to +150	°C
Operating junction temperature range	T_J	-40 to +125	°C
Repetitive peak pulse current	I_{PP}	see next table	A

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Symbol	Parameter
V_{DRM}	Peak off-state voltage
I_{DRM}	Off-state current
V_S	Switching voltage
I_S	Switching current
V_T	On-state voltage
I_T	On-state current
I_H	Holding current
C_O	Off-state capacitance



MARKING

CP42B : Device Marking Code
1409: In ninth week, 2014

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, continued)

Part Number	$I_{DRM}@V_{DRM}$		$V_S^{(1)}@I_S$		$V_T@I_T$		I_H	$C_O^{(2)}$	Marking
	μA	V	V	mA	V	A	mA	pF	
	max		max	max	max	max	max	max	
CP4200SB	1	400	520	800	4	2.2	100	35	CP42B
CP4200SC	1	400	520	800	4	2.2	100	35	CP42C
CP4200SD	1	400	520	800	4	2.2	100	40	CP42D

(1) V_s is measured at 100KV/s

(2) Off-state capacitance is measured in $V_{DC}=2\text{V}$, $V_{RMS}=1\text{V}$, $f=1\text{MHz}$

SURGE RATINGS

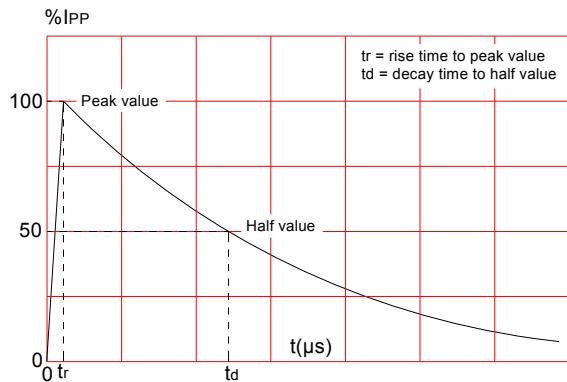
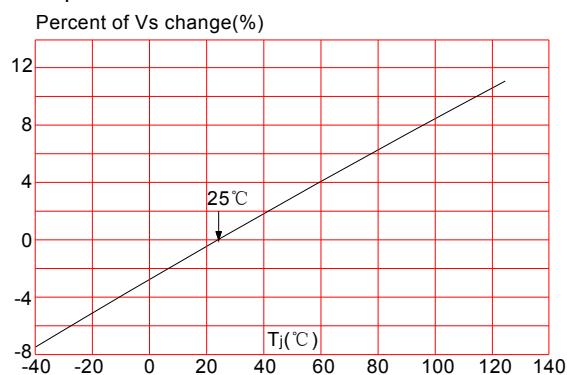
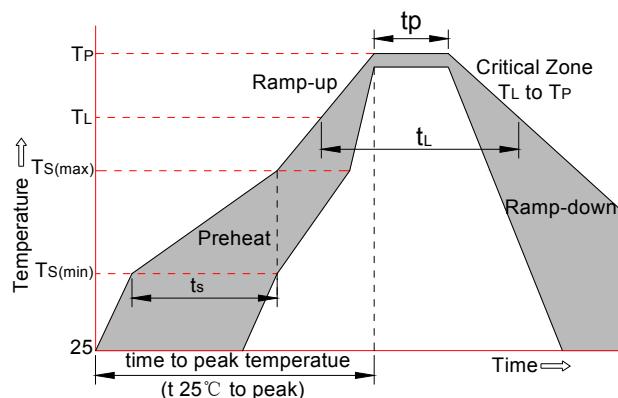
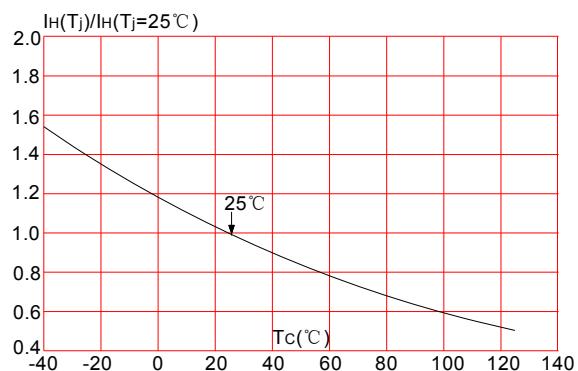
Surge peak	Series		
	B	C	D
	$I_{PP} (\text{A}) \text{ min}$	$I_{PP} (\text{A}) \text{ min}$	$I_{PP} (\text{A}) \text{ min}$
5/320μs (10/700μs)	100	150	200
8/20μs (1.2/50μs)	250	400	600
2/10μs	250	500	800
10/1000μs	80	100	200

ORDERING INFORMATION

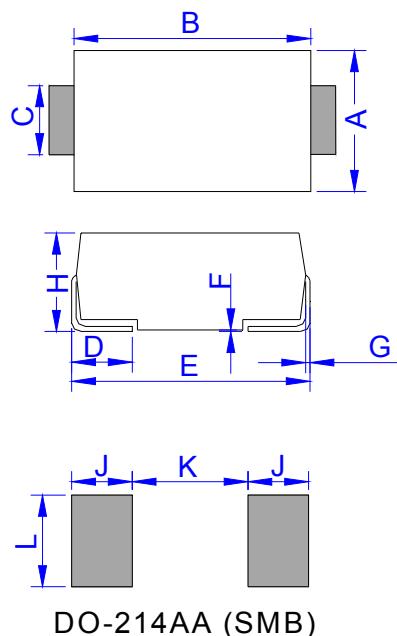
CP	420	0	S	B
Low capacitance sidac				Surge Ratings
	Median Voltage			
		0:Bi-direction, 1:Uni		Package type:SMB

SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see FIG.2)
Pre Heat	-Temperature Min ($T_{s(\min)}$)	+150°C
	-Temperature Max($T_{s(\max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L)to peak)		3°C/sec. Max
$T_{s(\max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C

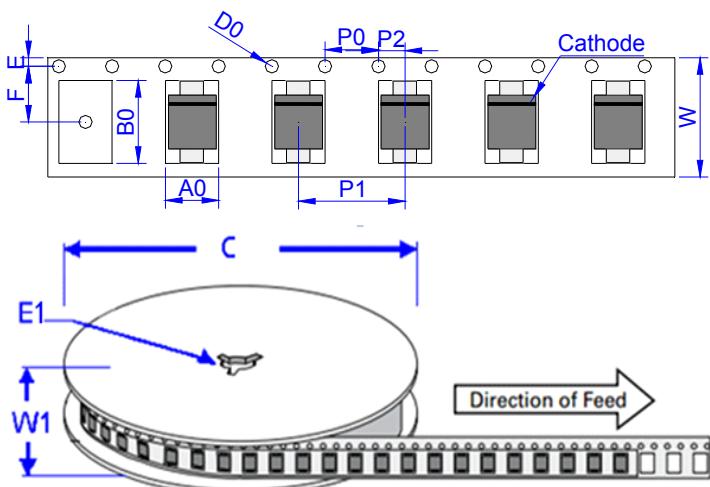
FIG.1: $tr \times td$ pulse waveform**FIG.3:** Normalized Vs change vs. junction temperature**FIG.2:** Reflow condition**FIG.4:** Normalized DC holding current vs. case temperature

PACKAGE MECHANICAL DATA



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.30	3.94	0.130	0.155
B	4.30	4.80	0.169	0.189
C	1.90	2.20	0.075	0.087
D	0.95	1.52	0.037	0.060
E	5.20	5.60	0.205	0.220
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
H	2.10	2.40	0.083	0.094
J	2.20		0.087	
K		2.60		0.102
L	2.30		0.091	

TAPE AND REEL SPECIFICATION-SMB



Ref.	Dimensions	
	Millimeters	Inches
A0	3.76 ± 0.3	0.148 ± 0.012
B0	5.69 ± 0.3	0.224 ± 0.012
C	330.0	13.0
D0	1.55 ± 0.1	0.061 ± 0.004
E	1.75 ± 0.2	0.069 ± 0.008
E1	13.3 ± 0.3	0.524 ± 0.012
F	5.5 ± 0.2	0.217 ± 0.008
P0	4.00 ± 0.2	0.157 ± 0.008
P1	8.00 ± 0.2	0.3145 ± 0.008
P2	2.00 ± 0.2	0.079 ± 0.008
W	12.0 ± 0.2	0.472 ± 0.008
W1	15.7 ± 2.0	0.618 ± 0.079

OUTLINE	UNIT WEIGHT (g/PCS) typ.	REEL (PCS)	PER CARTON (PCS)	REEL DIAMETERS (mm)
TAPING	0.098	3,000	48,000	330

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